

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q80166

Masato KOBAYAKAWA, et al.

Appln. No.: 10/589,610

Group Art Unit: 2811

Confirmation No.: 8635

Examiner: Ngan V. NGO

Filed: August 16, 2006

For: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER  
STRUCTURE AND PRODUCTION METHOD THEREOF

**RESPONSE TO RESTRICTION REQUIREMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Responsive to the outstanding Restriction Requirement of January 15, 2008, Applicant elects Group I, claims 1-23 (drawn to a semiconductor device), for prosecution, without traverse. Applicant reserves the right to request rejoinder of process claims including all the limitations of any allowable product claim pursuant to MPEP §821.04. Applicant also reserves the right to file a Divisional Application directed to the non-elected subject matter.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



Abraham J. Rosner  
Registration No. 33,276

SUGHRUE MION, PLLC  
Telephone: (202) 293-7060  
Facsimile: (202) 293-7860

WASHINGTON OFFICE

**23373**

CUSTOMER NUMBER

Date: February 1, 2008